



# 2SK1896

N-Channel Silicon MOSFET

DC-DC Converter, Motor Drive Applications

## Features

- Low ON resistance.
- Ultrahigh-speed switching.
- Low-voltage drive.
- Micaless package facilitating easy mounting.

## Specifications

### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		60	V
Gate-to-Source Voltage	V <sub>GSS</sub>		-20	V
Drain Current (DC)	I <sub>D</sub>		15	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	60	A
Allowable Power Dissipation	P <sub>D</sub>		2.0	W
		T <sub>c</sub> =25°C	25	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	60			V
Gate-to-Source Breakdown Voltage	V <sub>(BR)GSS</sub>	I <sub>G</sub> =-100 A, V <sub>DS</sub> =0	-20			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0			100	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =-16V, V <sub>DS</sub> =0			-10	μA
Cutoff Voltage	V <sub>GSS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.0		2.0	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =9A	8	13		S
Static Drain-to-Source ON-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =9A, V <sub>GS</sub> =10V		0.05	0.07	Ω
	R <sub>DS(on)</sub>	I <sub>D</sub> =9A, V <sub>GS</sub> =4V		0.07	0.095	Ω

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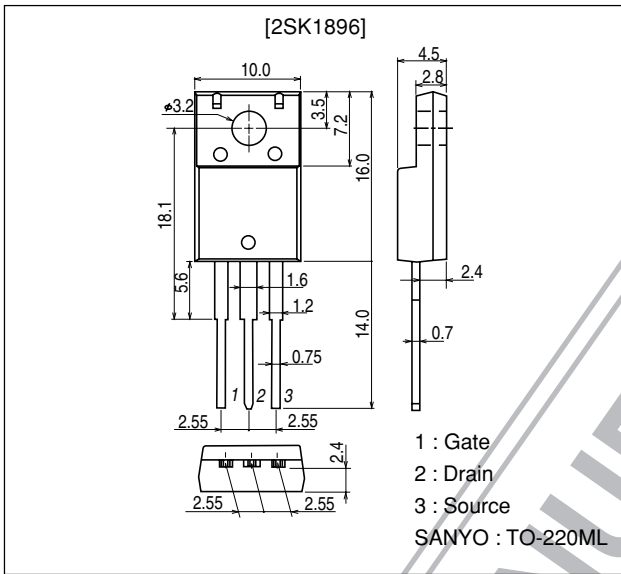
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	$C_{iss}$	$V_{DS}=20V, f=1MHz$		1230		pF
Output Capacitance	$C_{oss}$	$V_{DS}=20V, f=1MHz$		330		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=20V, f=1MHz$		65		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		14		ns
Rise Time	$t_r$	See specified Test Circuit		35		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		250		ns
Fall Time	$t_f$	See specified Test Circuit		120		ns
Diode Forward Voltage	$V_{SD}$	$I_S=15A, V_{GS}=0$		1.0	1.5	V

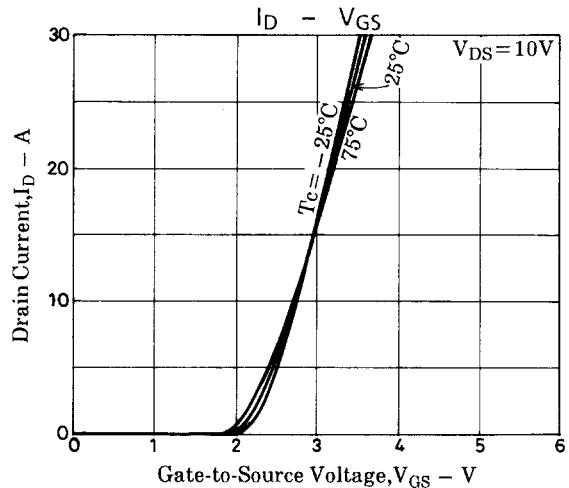
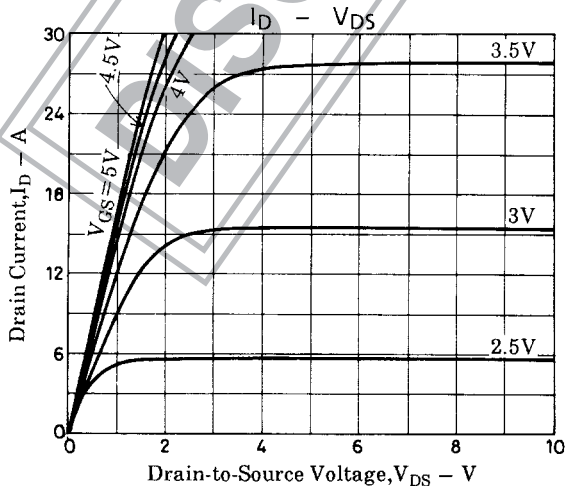
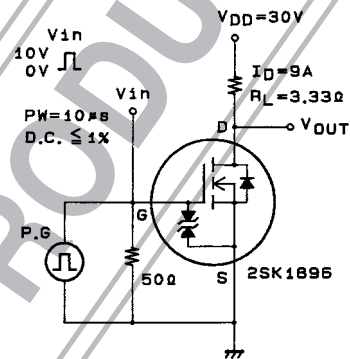
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unit:mm

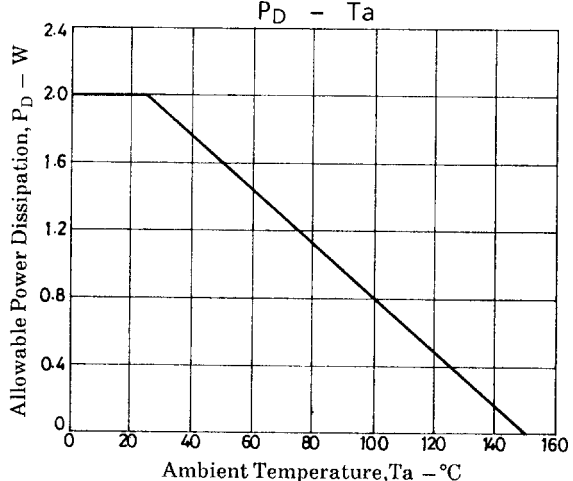
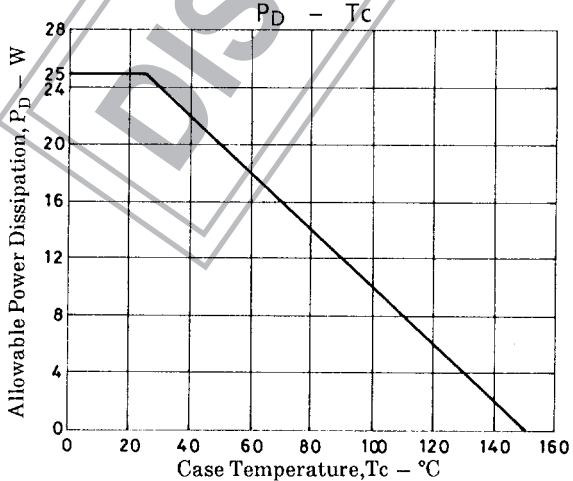
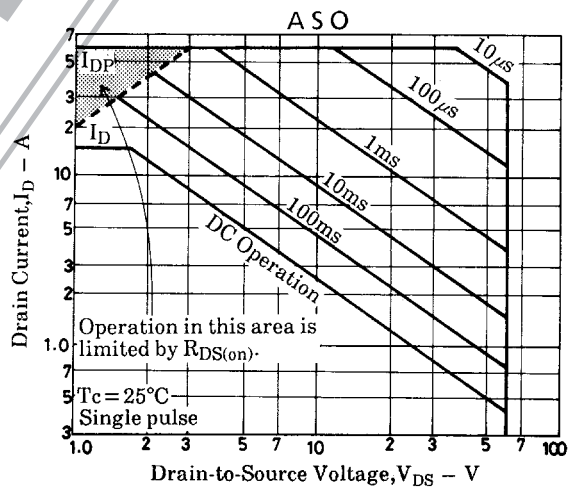
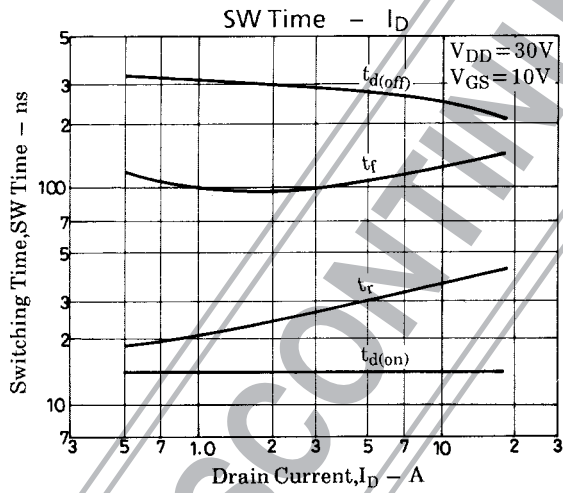
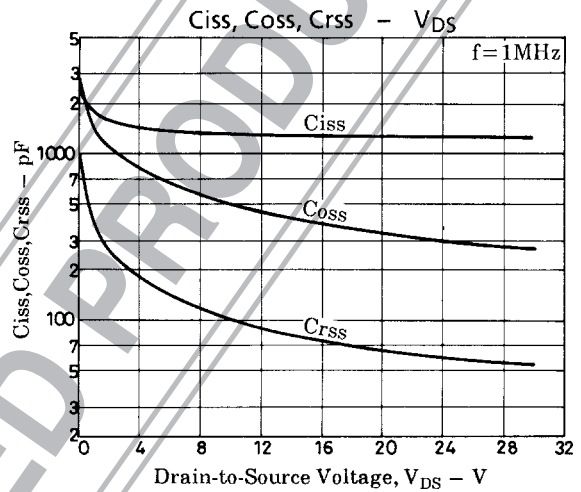
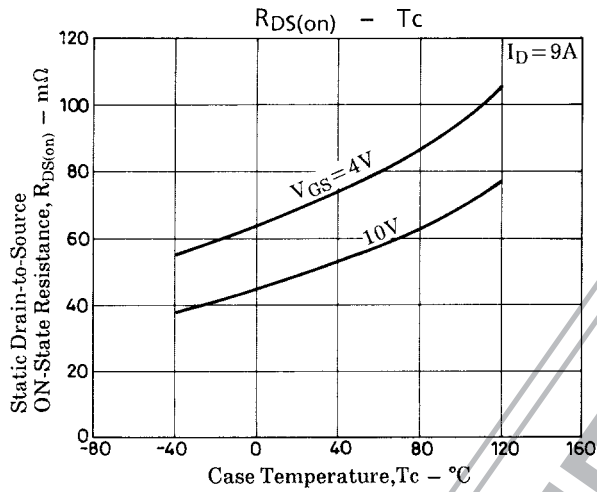
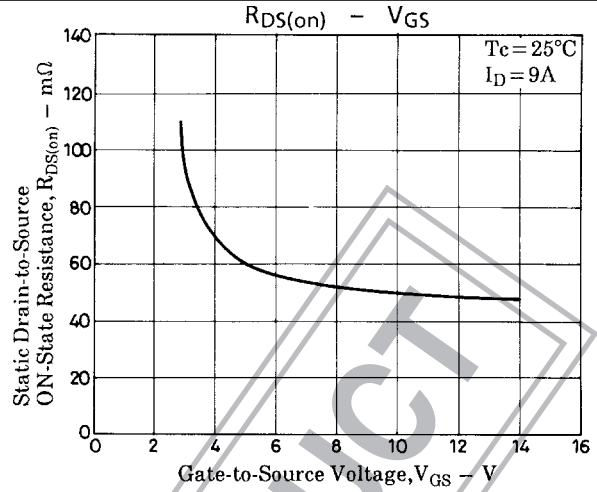
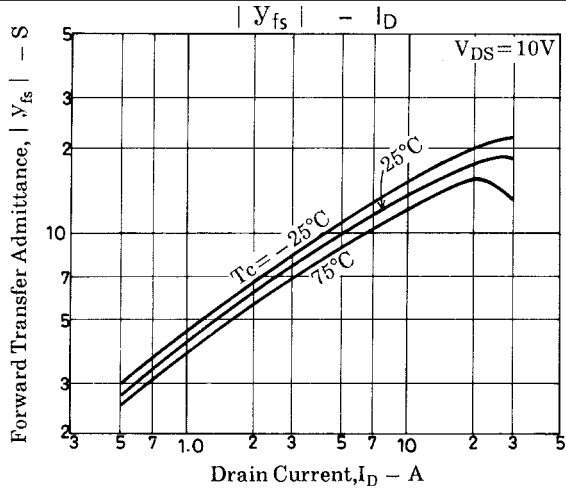
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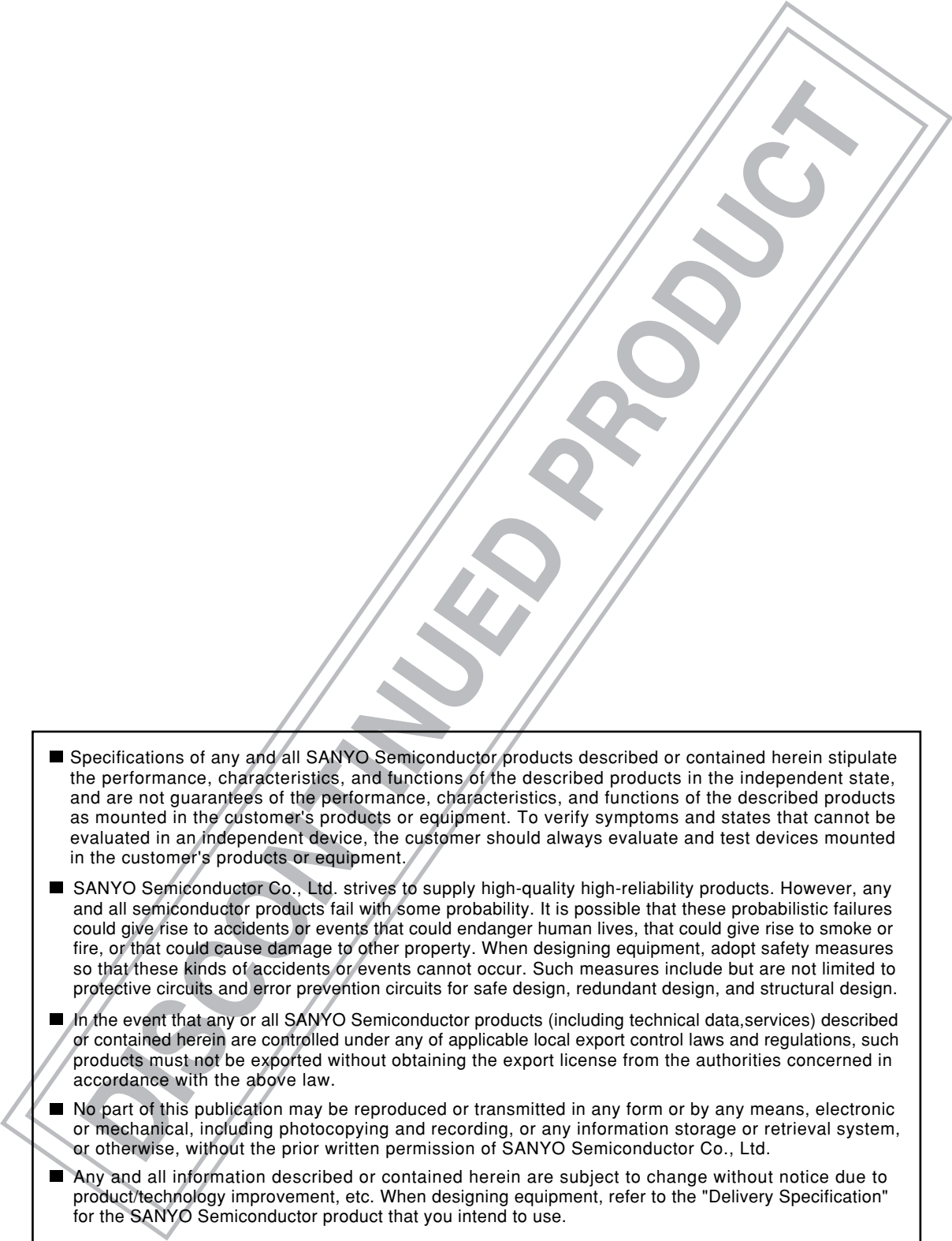


## Switching Time Test Circuit



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